



**DMP6350S** 

#### **Product Summary**

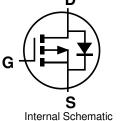
BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
001/	350mΩ @ V <sub>GS</sub> = -10V	-1.5A
-60V	550mΩ @ V <sub>GS</sub> = -4.5V	-1.2A

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

Top View



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D G S

**60V P-CHANNEL ENHANCEMENT MODE MOSFET** 

Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2) Halogen and Antimony Free. "Green" Device (Note 3) Qualified to AEC-Q101 Standards for High Reliability

Case Material: Molded Plastic, "Green" Molding Compound.

Terminals: Finish — Matte Tin Annealed over Copper Leadframe.

UL Flammability Classification Rating 94V-0 Moisture Sensitivity: Level 1 per J-STD-020

Solderable per MIL-STD-202, Method 208 3 Terminals Connections: See Diagram Below

Weight: 0.009 grams (Approximate)

**Features and Benefits** 

Low On-Resistance Low Input Capacitance Fast Switching Speed Low Input/Output Leakage

**Mechanical Data** 

Case: SOT23

Top View

#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMP6350S-7	SOT23	3,000/Tape & Reel
DMP6350S-13	SOT23	10,000/Tape & Reel

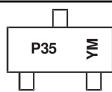
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

 See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



P35 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$ = Year (ex: D = 2016) M = Month (ex: 9 = September)

#### Date Code Key

Notes:

Year	2015	2016	2017	2018	2019	2020	2021	2022
Code	С	D	E	F	G	Н	Ι	J

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



#### Maximum Ratings (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	-60	V		
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Drain Current (Note 6), $V_{GS}$ = -10V	Steady State	$\begin{array}{l} T_A=+25^\circ C\\ T_A=+70^\circ C \end{array}$	ID	-1.5 -1.2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle =	IDM	-6	А		

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	0.72	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 5)	R <sub>0JA</sub>	176	°C/W
Power Dissipation (Note 6)	PD	1.17	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 6)	R <sub>0JA</sub>	108	°C/W
Thermal Resistance, Junction to Case	R <sub>eJC</sub>	34	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	٥°

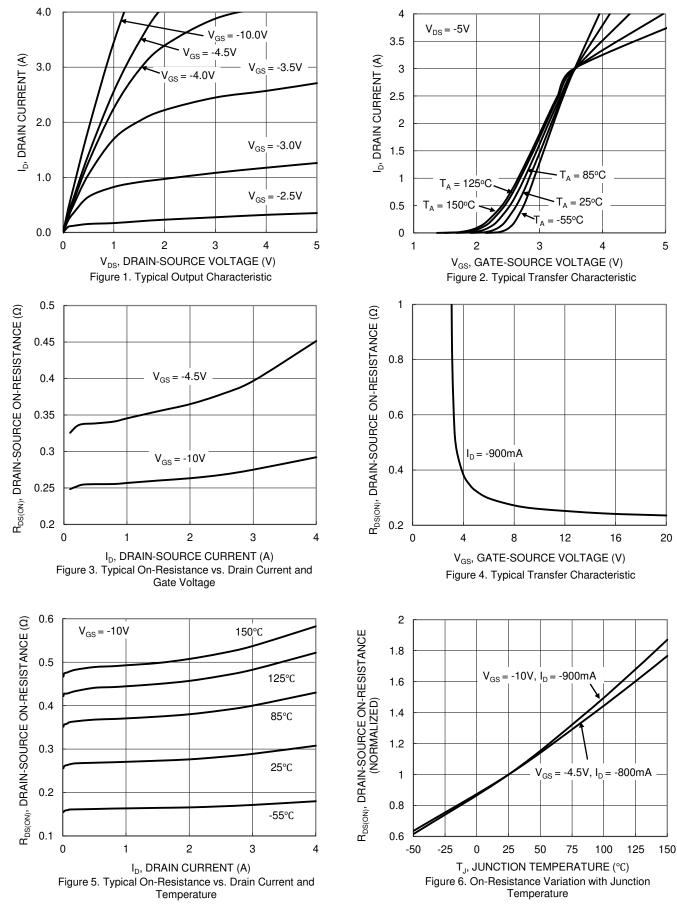
#### Electrical Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current TJ = +25°C	I <sub>DSS</sub>	I	-	-1.0	μA	$V_{DS} = -60V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	-1.8	-3.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
Static Drain-Source On-Resistance			257	350	mΩ	$V_{GS} = -10V, I_D = -0.9A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	343	550	11152	$V_{GS} = -4.5V, I_D = -0.8A$
Diode Forward Voltage	V <sub>SD</sub>	-	-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>	-	206	-	pF	
Output Capacitance	Coss	-	15	-	pF	$V_{DS} = -30V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	-	11	-	pF	1 = 1.00012
Gate Resistance	R <sub>g</sub>	-	17	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	-	2.0	-	nC	
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	-	4.1	-	nC	V <sub>DS</sub> = -30V, I <sub>D</sub> = -0.9A
Gate-Source Charge	Q <sub>gs</sub>	-	0.5	-	nC	$v_{\rm DS} = -30 v, I_{\rm D} = -0.9 A$
Gate-Drain Charge	Q <sub>gd</sub>	-	0.8	-	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	-	3.6	-	ns	
Turn-On Rise Time	t <sub>R</sub>	-	3.8	-	ns	$V_{DD} = -30V, V_{GS} = -10V,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	12.3	-	ns	$I_{D} = -1.0A, R_{g} = 6\Omega$
Turn-Off Fall Time	t <sub>F</sub>	-	7.3	-	ns	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	-	8.2	-	ns	I <sub>S</sub> = -1.0A, di/dt = -100A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	-	2.7	-	nC	I <sub>S</sub> = -1.0A, di/dt = -100A/µs

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.



#### **DMP6350S**



DMP6350S Document number: DS38474 Rev. 3 - 2 3 of 7 www.diodes.com



#### **DMP6350S**

 $I_D = -1mA$ 

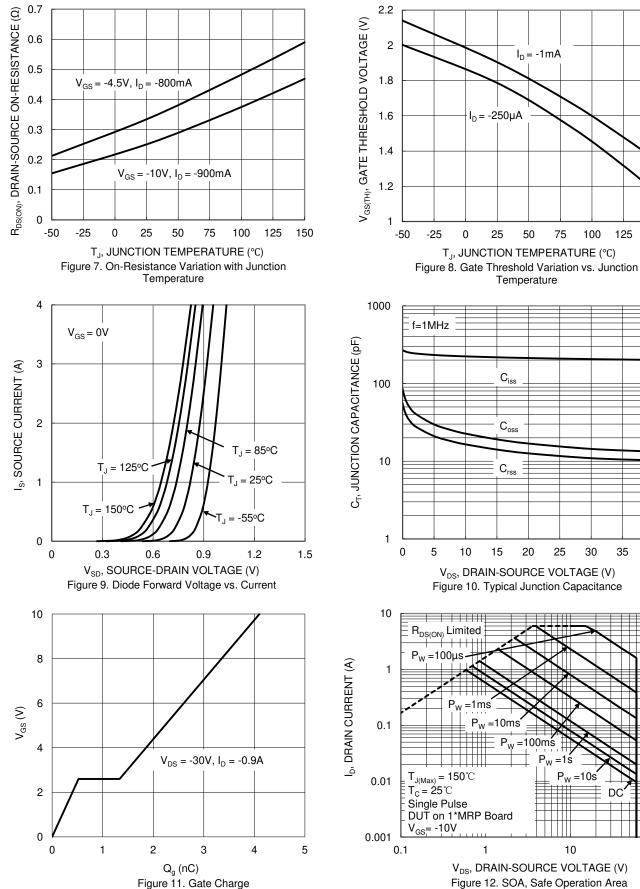
50

75

100

125

150



20

25

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35

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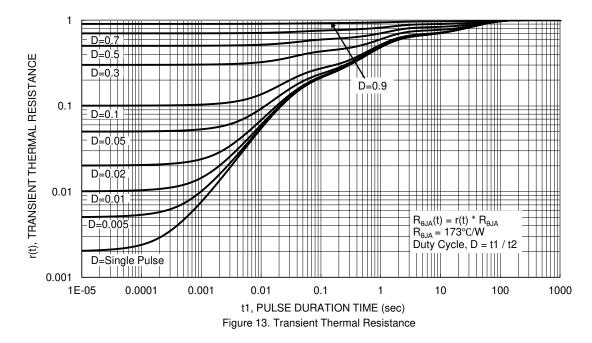
V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area

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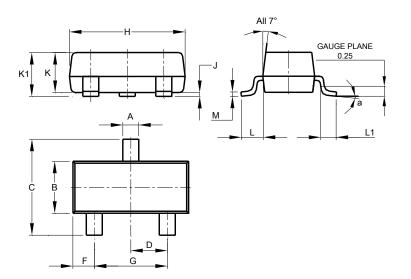




### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

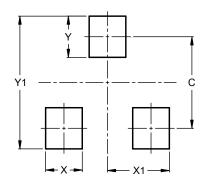


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Dim	Min	Max	Тур
Α	0.37	0.51	0.40
В	1.20	1.40	1.30
С	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
К	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
Μ	0.085	0.150	0.110
а	0°	8°	
All	Dimens	ions in	mm

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



 Dimensions
 Value (in mm)

 C
 2.0

 X
 0.8

 X1
 1.35

 Y
 0.9

 Y1
 2.9



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